Silicon PNP transistor in a TO-3P Plastic Package.

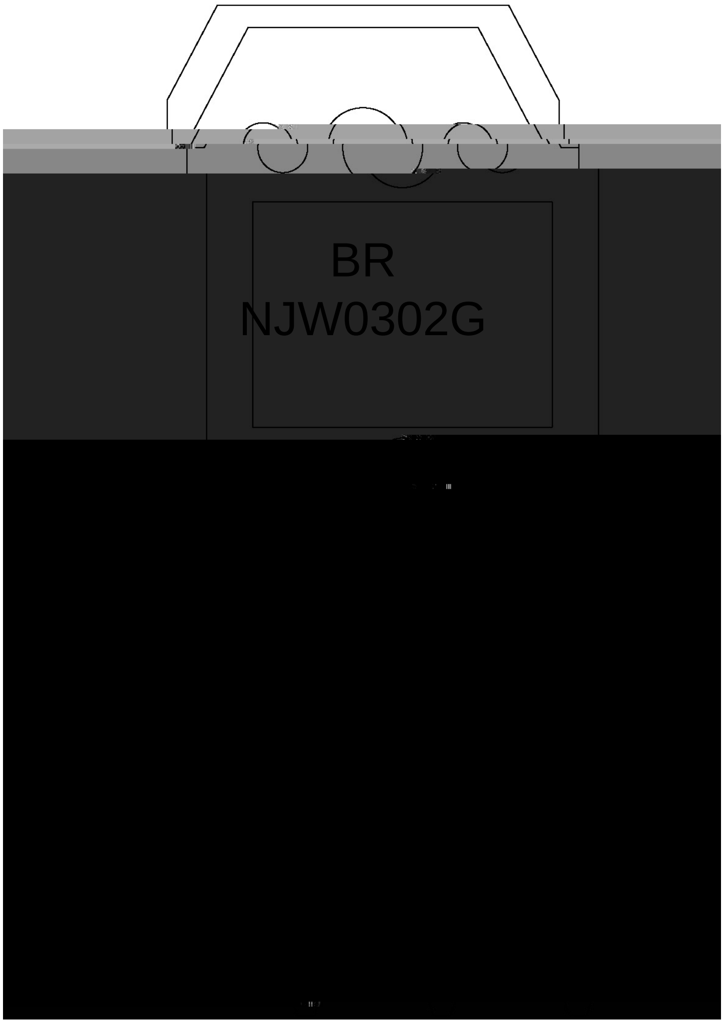
Recommend for 100W high fidelity audio frequency amplifier output stage, Complementary to

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-230	V
Collector to Emitter Voltage	V_{CEO}	-230	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collector Current - Continuous	I_C	-15	A
Peak Collector Current	I_{CP}	-30	A
Base Current	I_B	-1.5	A
Collector Power Dissipation	$P_{C(TC=25\ )}$	150	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-50mA I_B=0	-230			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-230V I_E=0			-5.0	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-5.0V I_C=0			-5.0	μA
DC Current Gain	$h_{FE(1)}$	V_{CE}=-5.0V I_C=-1.0A	55		160	
	$h_{FE(2)}$	V_{CE}=-5.0V I_C=-7.0A	35	60		
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-8.0A I_B=-0.8A		-1.5	-3.0	V
Base to Emitter Voltage	V_{BE}	V_{CE}=-5.0V I_C=-7.0A		-1.0	-1.5	V
Transition Frequency	f_T	I_C=-1.0A V_{CE}=-5.0V		30		MHz

/ Electrical Characteristic Curve

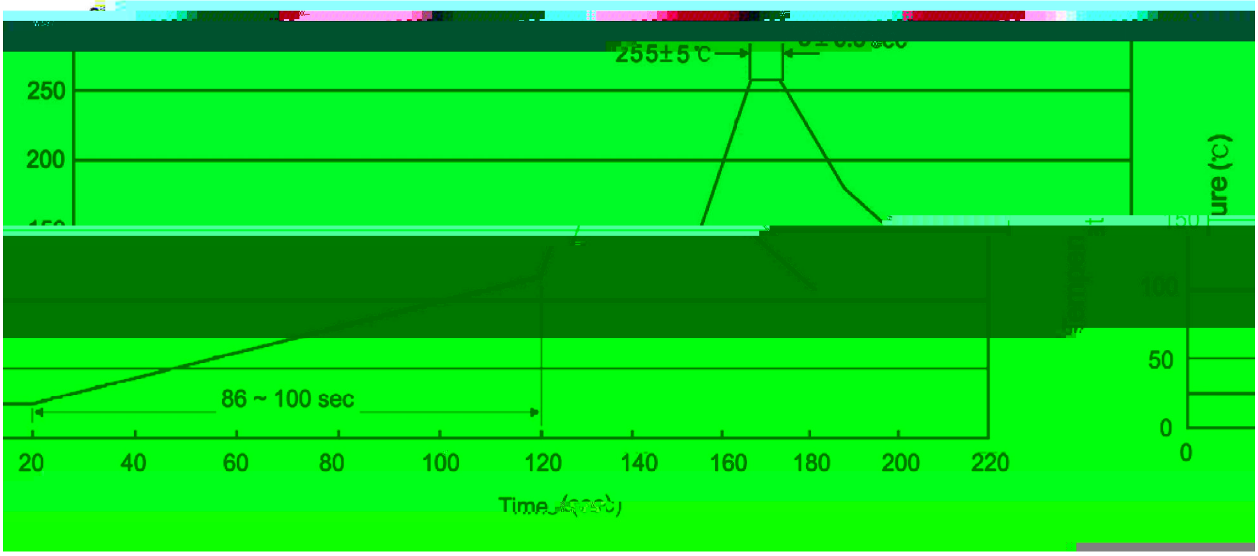
/ Marking Instructions



Note:

BR:	Company Code.
NJW0302G:	Product Type.
****:	Lot No. Code, code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)



	Note:
1 25 150 60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2 255 5 5 0.5sec;	2.Peak Temp.:255 5 , Duration:5 0.5sec.
3 2 10 /sec.	3. Cooling Speed: 2~10 /sec.

'H 4sDimens4 T9914406(d: 2~1)-f 1 (10)20.65 11R Tf 1.6632 0 86 367116d>T745<045 54ca-5.7